Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in this application.

Listing of Claims:

1. (Previously Presented) A device, comprising:

a material of a first conductivity type;

a first transistor in the material;

a body contact region in the material;

a resistance region disposed in the material between the first transistor and the body contact region to substantially electrically isolate the first transistor from the body contact region, the resistance region having a resistivity higher than a resistivity of the material, wherein the resistance region has a non-zero impurity concentration lower than an impurity concentration of the material; and

a discrete capacitor coupled between a body and a source of the first transistor.

2. (Previously Presented) The device of claim 1, further comprising:

a second transistor disposed in the material, wherein the second transistor is disposed on a same side of the resistance region as the body contact region.

3. (Original) The device of claim 1, wherein the body contact region is adapted to be coupled to ground and the first conductivity type is p-type.

4. (Original) The device of claim 1, wherein the body contact region is adapted to be coupled to a power supply voltage and the first conductivity type is n-type.

5. (Previously Presented) The device of claim 1, further comprising a substrate, the material being on the substrate.

6.-7. (Cancelled)

8. (Previously Presented) The device of claim 1, wherein the resistance region occupies substantially an entire cross-sectional area of the material between the first transistor and the body contact region.

9. (Previously Presented) A device, comprising:

a material of a first conductivity type;

a first transistor in the material;

a body contact region in the material;

a resistance region in the material between the first transistor and the body contact region to substantially electrically isolate the first transistor from the body contact region, the resistance region having a resistivity higher than a resistivity of the material;

a second transistor coupled in series with the first transistor and having a control electrode adapted to receive an input signal of the device, the first transistor having a control electrode adapted to receive a bias voltage, and the body contact region being adapted to be coupled to a first one of a power supply voltage and ground; and

a load having a first end coupled to the first transistor and a second end adapted to be coupled to a second one of the power supply voltage and ground, a body of the second transistor being adapted to be coupled to the first one of the power supply voltage and ground.

10. (Original) The device of claim 9, wherein the first and second transistors are n-type conductivity transistors.

11. (Original) The device of claim 9, wherein the resistance region is adapted to substantially isolate a body of the first transistor from ground.

12. (Original) The device of claim 9, wherein the resistance region is adapted to substantially isolate a body of the first transistor from ground when the input signal is at or above a predetermined operating frequency.

13. (Original) The device of claim 9, wherein the load is an inductance.

14. (Previously Presented) The device of claim 1, wherein the material is an epitaxial layer.

15.-26. (Cancelled)

27. (Currently Amended) The device of claim [[26]] 32, wherein the resistance region substantially isolates the first transistor from the body contact region.

28. (Cancelled)

29. (Currently Amended) The device of claim [[26]] 32, wherein the body contact region is adapted to be coupled to ground.

30. (Currently Amended) The device of claim [[26]] 32, wherein the material is an epitaxial layer.

31. (Currently Amended) The device of claim [[26]] 32, wherein the resistance region has an impurity concentration lower than an impurity concentration of the material.

32. (Currently Amended) A device, comprising:
a material of a first conductivity type formed directly on a semiconductor substrate;
a first transistor in the material;

a body contact region in the material;

a resistance region disposed in the material between the first transistor and the body contact region, the resistance region having a resistivity higher than a resistivity of the material, wherein the semiconductor substrate is of said first conductivity type;

a second transistor in the material, wherein the second transistor is on a same side of the resistance region as the body contact region; and

~~The device of claim 26, further comprising~~ a discrete capacitor coupled between a body and a source of the first transistor.

33. (Currently Amended) The device of claim [[26]] 32, wherein the resistance region occupies substantially an entire cross-sectional area of the material between the first transistor and the body contact region.

34.-37. (Cancelled)

38. (Previously Presented) A device, comprising:

a material of a first conductivity type;

a first transistor in the material;

a body contact region in the material;

a resistance region in the material between the first transistor and the body contact region, the resistance region having a resistivity higher than a resistivity of the material, wherein the resistance region comprises the same material as said material but has a non-zero impurity concentration lower than an impurity concentration of said material; and

a second transistor in the material, wherein the second transistor is disposed on a same side of the resistance region as the body contact region.

39. (Previously Presented) The device of claim 38, further comprising a substrate, the material being on the substrate.

40. (Previously Presented) The device of claim 38, wherein the material is an epitaxial layer deposited on a substrate.

41. (Cancelled)